NSN 5961-01-302-9022

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-302-9022 **Inclosure Material:** Ceramic **Overall Length:** Between 0.660 inches and 0.785 inches **Terminal Length:** 0.100 inches **Overall Height:** 0.200 inches **Overall Width:** 0.325 inches **End Application:** Inertial measuring unit, litton **Response Time:** 45.0 nanoseconds all transistor **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 100.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source all transistor and 30.0 gate to source voltage all transistor **Current Rating Per Characteristic:** 4.00 amperes off-state current, peak all transistor **Power Rating Per Characteristic:** 4.0 watts total device dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Test Data Document:** 06841-932548 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 14 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Fiig: A110a0

No